

Silicon PNP Power Transistor

2SB1097

DESCRIPTION

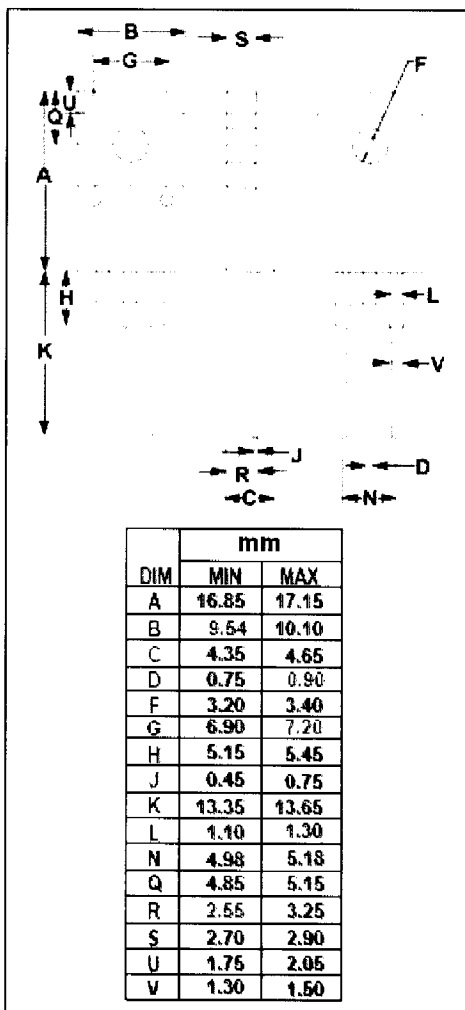
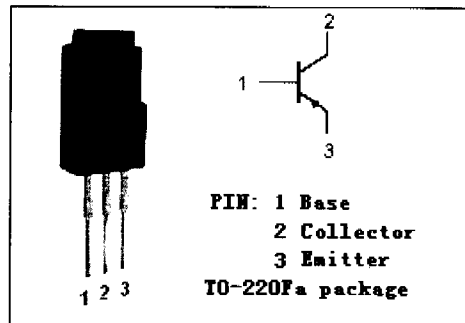
- High Collector Current: $I_C = -7A$
- Low Collector Saturation Voltage
 $V_{CE(sat)} = -0.5V(\text{Max}) @ I_C = -5A$
- Complement to Type 2SD1588

APPLICATIONS

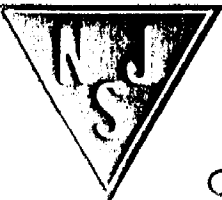
- Designed for low-frequency power amplifiers and low speed switching applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Pulse	-15	A
I_B	Base Current-Continuous	-3.5	A
P_C	Total Power Dissipation @ $T_a = 25^\circ C$	2	W
	Total Power Dissipation @ $T_c = 25^\circ C$	30	
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5A; I_B = -0.5A$			-0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -5A; I_B = -0.5A$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -60V; I_E = 0$			-10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5V; I_C = 0$			-10	μA
h_{FE-1}	DC Current Gain	$I_C = -3A; V_{CE} = -1V$	40		200	
h_{FE-2}	DC Current Gain	$I_C = -5A; V_{CE} = -1V$	20			

◆ h_{FE-1} Classifications

M	L	K
40-80	60-120	100-200